

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE ( $\pi$ -MOSIII)

# 2SK2718

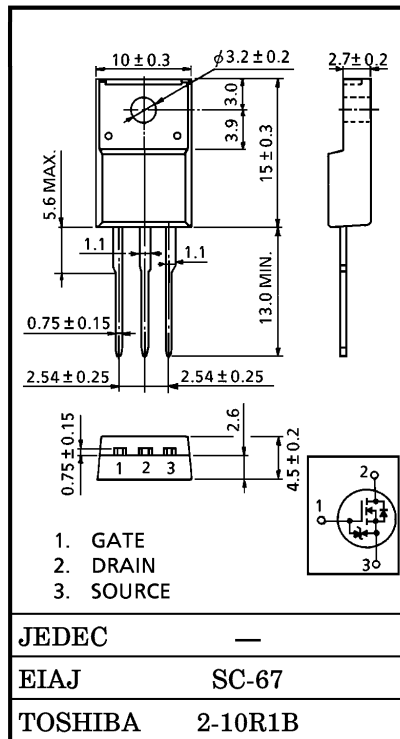
HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS  
DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS  
Unit in mm

- Low Drain-Source ON Resistance :  $R_{DS(ON)} = 5.6\Omega$  (Typ.)
- High Forward Transfer Admittance :  $|Y_{fs}| = 2.0S$  (Typ.)
- Low Leakage Current :  $I_{DSS} = 100\mu A$  (Max.) ( $V_{DS} = 720V$ )
- Enhancement-Mode :  $V_{th} = 2.0 \sim 4.0V$  ( $V_{DS} = 10V, I_D = 1mA$ )

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Drain-Source Voltage	$V_{DSS}$	900	V	
Drain-Gate Voltage ( $R_{GS} = 20k\Omega$ )	$V_{DGR}$	900	V	
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V	
Drain Current	DC	$I_D$	2.5	A
	Pulse	$I_{DP}$	7.5	A
Drain Power Dissipation ( $T_c = 25^\circ C$ )	$P_D$	40	W	
Single Pulse Avalanche Energy**	$E_{AS}$	216	mJ	
Avalanche Current	$I_{AR}$	2.5	A	
Repetitive Avalanche Energy*	$E_{AR}$	4.0	mJ	
Channel Temperature	$T_{ch}$	150	$^\circ C$	
Storage Temperature Range	$T_{stg}$	$-55 \sim 150$	$^\circ C$	



JEDEC	—
EIAJ	SC-67
TOSHIBA	2-10R1B

Weight : 1.9g

Thermal Characteristics

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	3.125	$^\circ C / W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	62.5	$^\circ C / W$

Note ;

\* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

\*\*  $V_{DD} = 90V$ , Starting  $T_{ch} = 25^\circ C$ ,  $L = 63.4mH$   
 $R_G = 25\Omega$ ,  $I_{AR} = 2.5A$  (See Figure)

**This transistor is an electrostatic sensitive device.  
Please handle with caution.**

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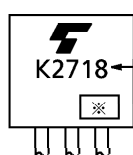
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		$I_{GSS}$	$V_{GS} = \pm 25V, V_{DS} = 0V$	—	—	$\pm 10$	$\mu A$
Gate-Source Breakdown Voltage		$V_{(BR)GSS}$	$I_G = 10\mu A, V_{DS} = 0V$	$\pm 30$	—	—	V
Drain Cut-off Current		$I_{DSS}$	$V_{DS} = 720V, V_{GS} = 0V$	—	—	100	$\mu A$
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = 10mA, V_{GS} = 0V$	900	—	—	V
Gate Threshold Voltage		$V_{th}$	$V_{DS} = 10V, I_D = 1mA$	2.0	—	4.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 1.5A$	—	5.6	6.4	$\Omega$
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 20V, I_D = 1.5A$	1.0	2.0	—	S
Input Capacitance		$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1MHz$	—	510	—	pF
Reverse Transfer Capacitance		$C_{rss}$		—	10	—	
Output Capacitance		$C_{oss}$		—	55	—	
Switching Time	Rise Time	$t_r$	<p><math>I_D = 1.5A</math> <math>V_{GS} = 10V</math> <math>R_L = 267\Omega</math> <math>V_{DD} \doteq 400V</math></p>	—	20	—	ns
	Turn-on Time	$t_{on}$		—	60	—	
	Fall Time	$t_f$		—	40	—	
	Turn-off Time	$t_{off}$		$V_{IN} : t_r, t_f < 5ns$ $Duty \leq 1\%, t_w = 10\mu s$	—	115	
Total Gate Charge (Gate-Source Plus Gate-Drain)		$Q_g$	$V_{DD} \doteq 400V, V_{GS} = 10V,$ $I_D = 2.5A$	—	21	—	nC
Gate-Source Charge		$Q_{gs}$		—	11	—	
Gate-Drain ("Miller") Charge		$Q_{gd}$		—	10	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	$I_{DR}$	—	—	—	2.5	A
Pulse Drain Reverse Current	$I_{DRP}$	—	—	—	7.5	A
Diode Forward Voltage	$V_{DSF}$	$I_{DR} = 2.5A, V_{GS} = 0V$	—	—	-2.0	V
Reverse Recovery Time	$t_{rr}$	$I_{DR} = 2.5A, V_{GS} = 0V$ $dI_{DR} / dt = 100A / \mu s$	—	960	—	ns
Reverse Recovery Charge	$Q_{rr}$		—	5.3	—	$\mu C$

MARKING

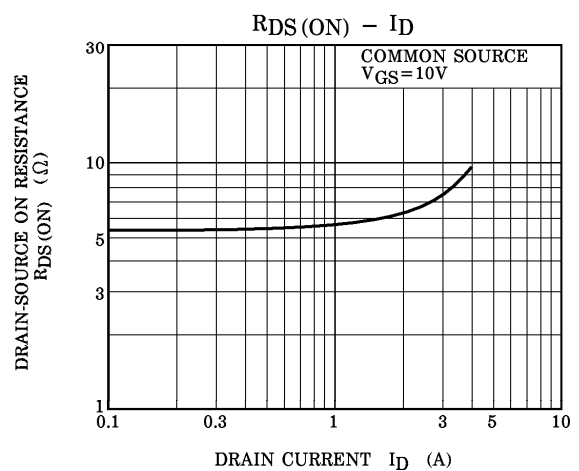
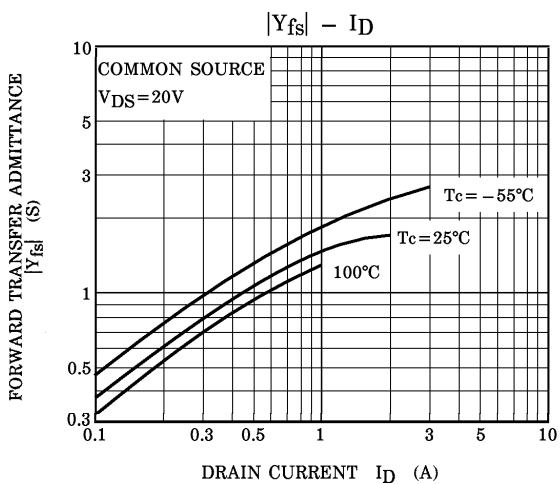
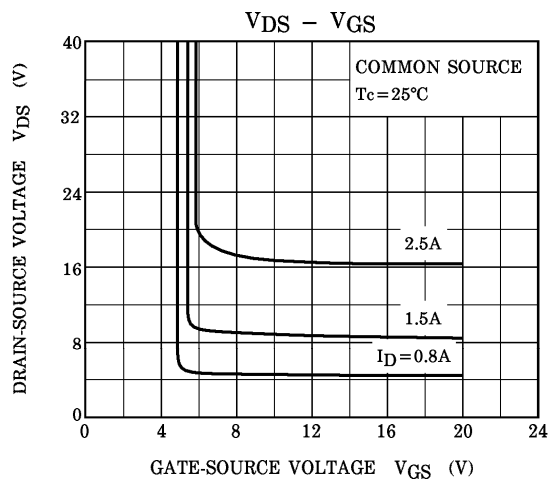
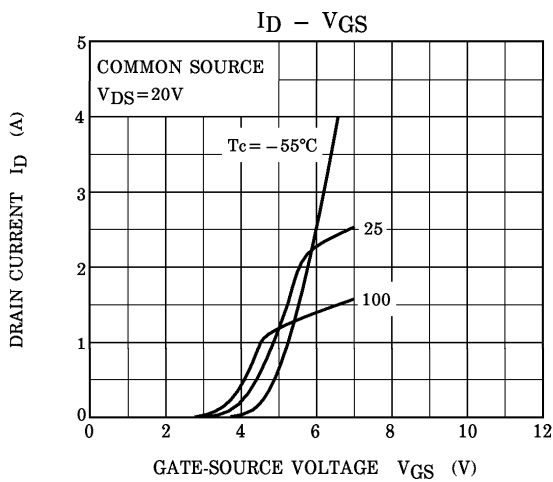
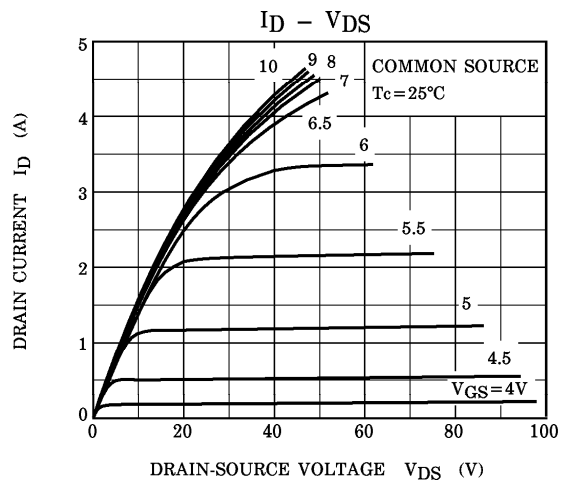
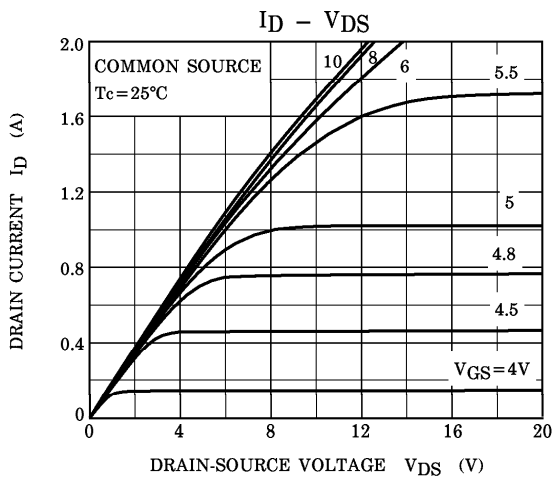


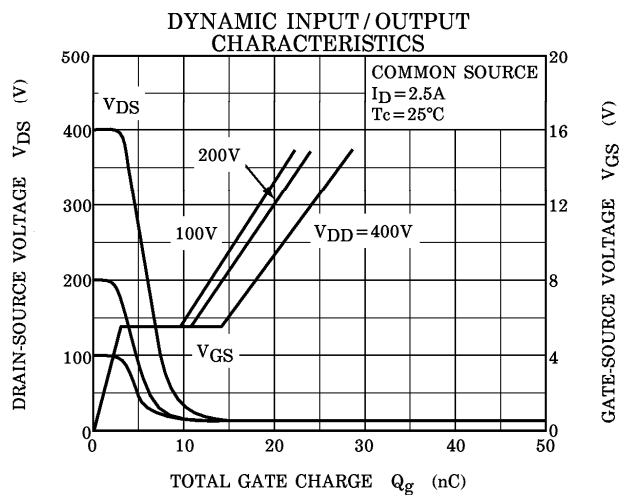
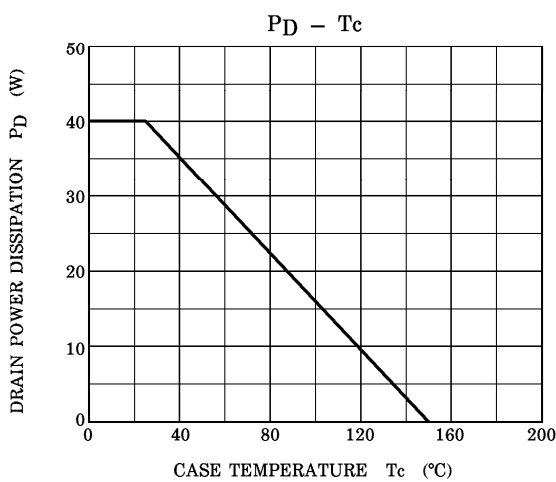
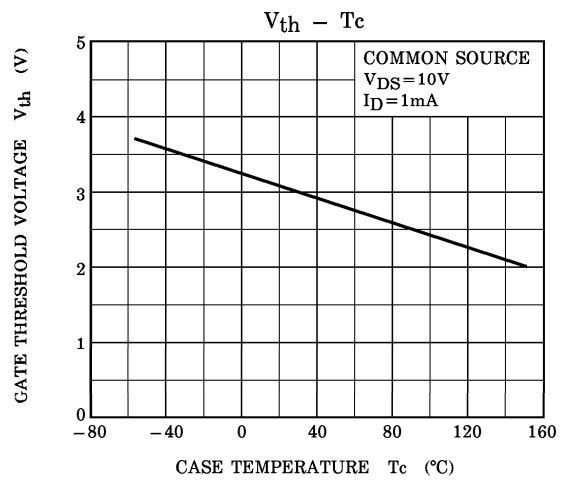
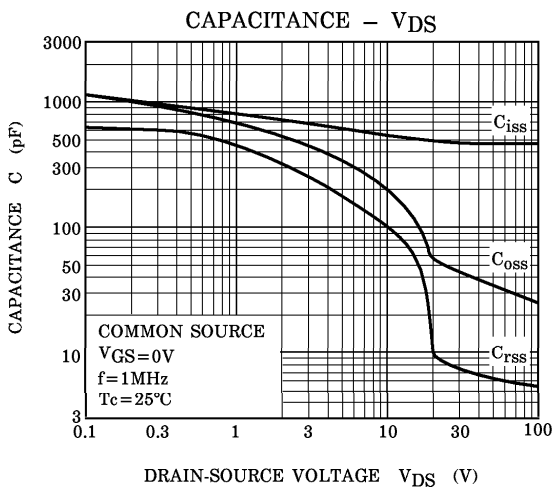
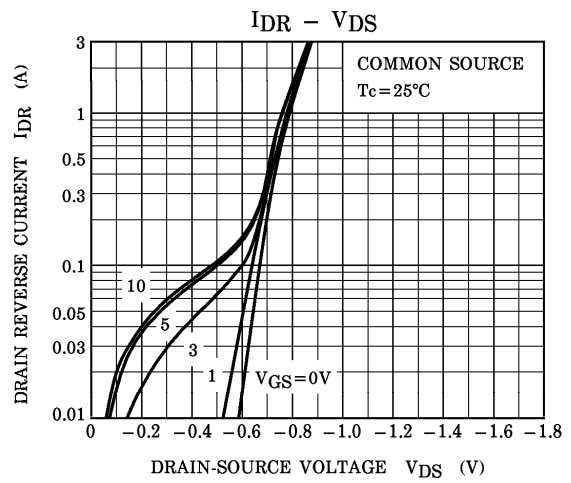
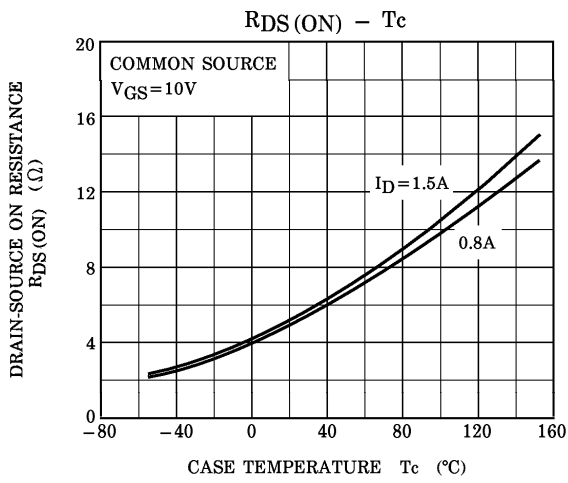
TYPE

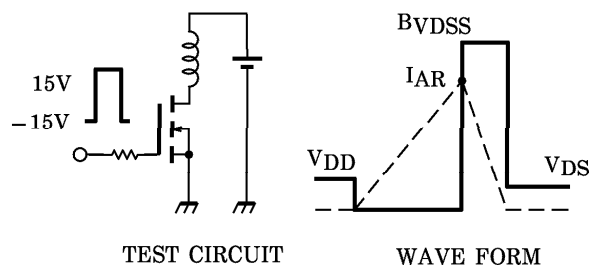
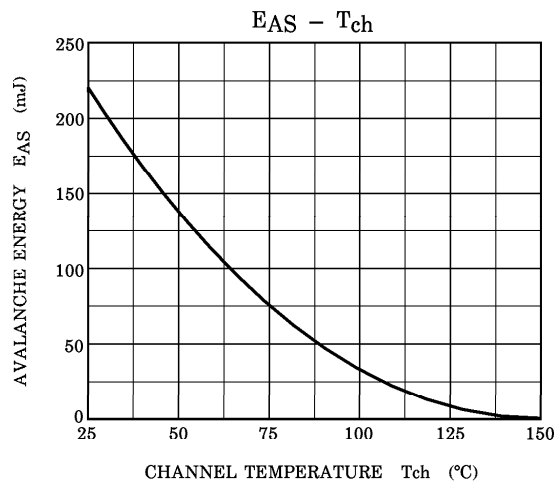
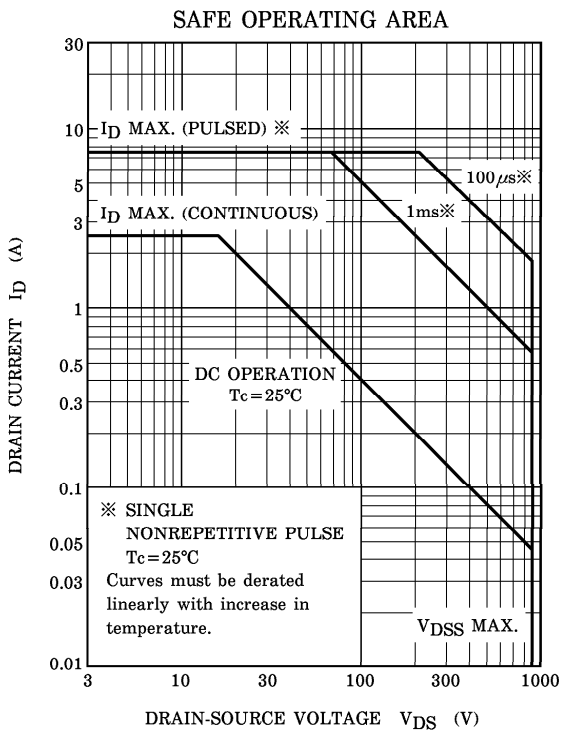
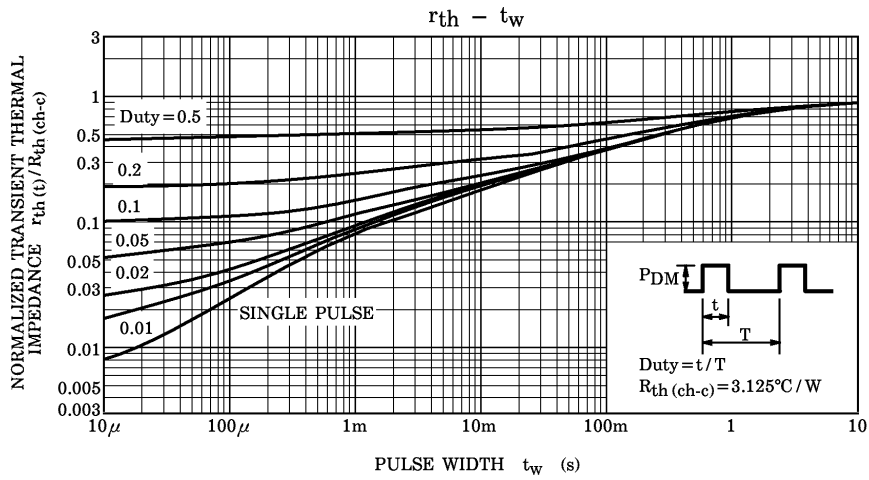
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







Peak  $I_{AR} = 2.5A$ ,  $R_G = 25\Omega$ ,  $V_{DD} = 90V$ ,  $L = 63.4mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$